

## Silicon Super Fast Recovery Diode

$V_{RRM} = 50\text{ V} - 600\text{ V}$

$I_F = 400\text{ A}$

### Features

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

Three Tower Package



### Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MURT40005 (R)	MURT40010 (R)	MURT40020 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		50	100	200	V
RMS reverse voltage	$V_{RMS}$		35	71	141	V
DC blocking voltage	$V_{DC}$		50	100	200	V
Continuous forward current	$I_F$	$T_C \leq 125\text{ }^\circ\text{C}$	400	400	400	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	3300	3300	3300	A
Operating temperature	$T_j$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MURT40005 (R)	MURT40010 (R)	MURT40020 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 200\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.3	1.3	1.3	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	25	25	25	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$	3	3	3	mA

### Recovery Time

Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{RR} = 0.25\text{ A}$	125	125	125	nS
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### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.14	0.14	0.14	$^\circ\text{C/W}$
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Figure .1- Typical Forward Characteristics

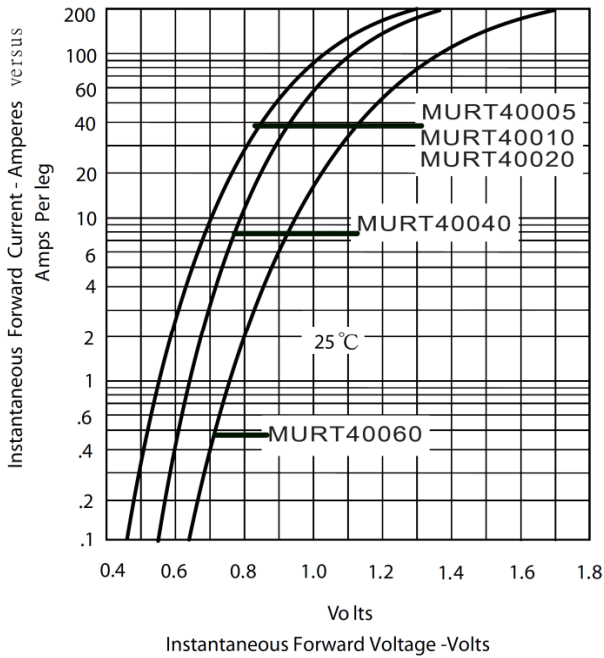


Figure .2- Forward Derating Curve

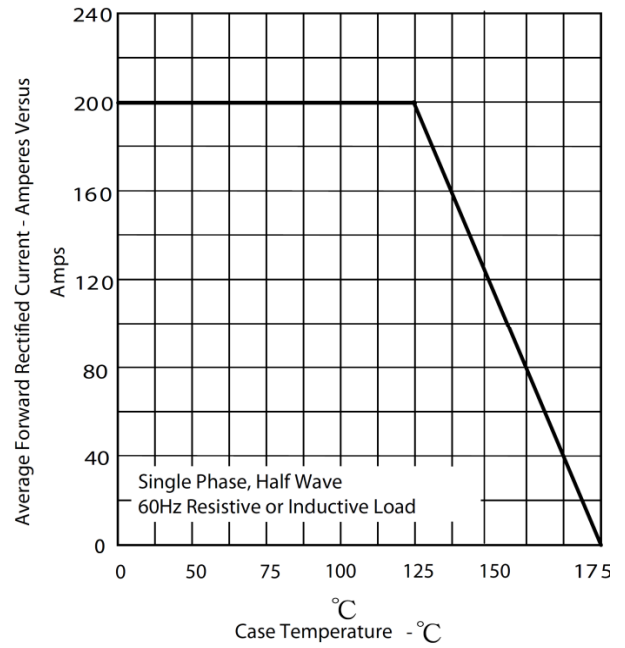


Figure.3- Peak Forward Surge Current

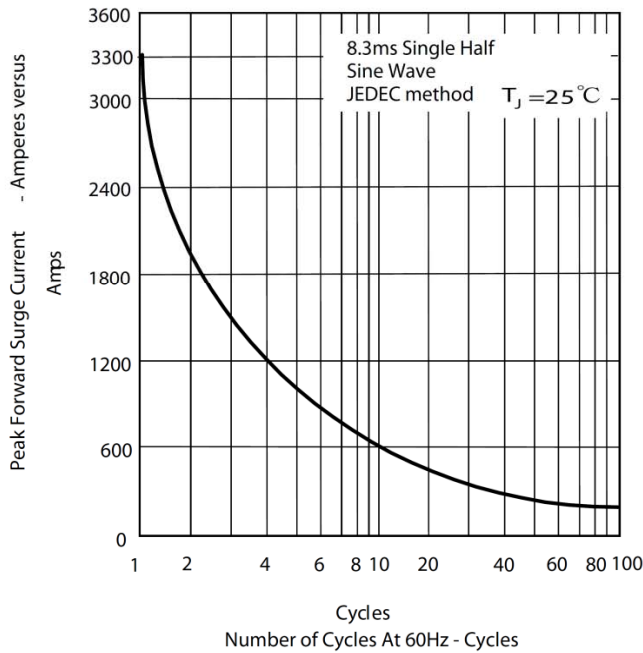


Figure.4- Typical Reverse Characteristics

